4V Drive Nch+Nch MOS FET

SP8K3

●Structure

Silicon N-channel MOS FET

Features

- 1) Low on-resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small surface Mount Package (SOP8).

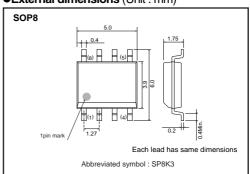
Application

Power switching, DC / DC converter.

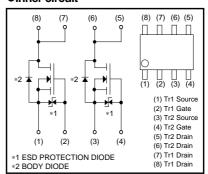
Packaging specifications

	Package	Taping
Type	Code	TB
	Basic ordering unit (pieces)	2500
SP8K3		0

●External dimensions (Unit : mm)



•Inner circuit



*A protection diode is included between the gate and the source terminals to protect the diode against static electricity when the product is in use. Use the protection circuit when the fixed voltages are exceeded.

● Absolute maximum ratings (Ta=25°C)

<It is the same ratings for the Tr1 and Tr2.>

Parameter		Symbol	Limits	Unit	
Drain-source voltage		V _{DSS}	30	V	
Gate-source voltage		V _{GSS}	20	V	
Drain current	Continuous	ID	±7.0	Α	
	Pulsed	I _{DP} *1	±28	Α	
Source current (Body diode)	Continuous	Is	1.6	Α	
	Pulsed	I _{SP} *1	6.4	Α	
Total power dissipation		P _D *2	2	W	
Channel temperature		Tch	150	°C	
Storage temperature		Tstg	-55 to +150	°C	

Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth (ch-a)*	62.5	°C/W

^{*}MOUNTED ON A CERAMIC BOARD.

^{*1} Pw≤10μs, Duty cycle≤1% *2 MOUNTED ON A CERAMIC BOARD.

●Electrical characteristics (Ta=25°C)

<It is the same characteristics for the Tr1 and Tr2.>

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	-	_	10	μΑ	Vgs=20V, Vps=0V
Drain-source breakdown voltage	V _{(BR) DSS}	30	_	_	V	I _D =1mA, V _{GS} =0V
Zero gate voltage drain current	IDSS	_	_	1	μΑ	V _{DS} =30V, V _{GS} =0V
Gate threshold voltage	V _{GS (th)}	1.0	_	2.5	V	V _{DS} =10V, I _D =1mA
Static drain-source on-state resistance	R _{DS (on)}	_	17	24	mΩ	I _D =7.0A, V _{GS} =10V
		_	23	33		I _D =7.0A, V _{GS} =4.5V
		-	25	35		I _D =7.0A, V _{GS} =4V
Forward transfer admittance	Y _{fs} *	5.0	_	_	S	I _D =7.0A, V _{DS} =10V
Input capacitance	Ciss	_	600	_	pF	V _{DS} =10V
Output capacitance	Coss	_	200	_	pF	Vgs=0V
Reverse transfer capacitance	Crss	_	120	_	pF	f=1MHz
Turn-on delay time	t _{d (on)} *	-	8	_	ns	I _D =3.5A, V _{DD} ≒15V
Rise time	tr *	_	10	_	ns	V _{GS} =10V
Turn-off delay time	t _{d (off)} *	_	37	_	ns	R _L =4.29Ω
Fall time	t _f *	-	11	_	ns	R _G =10Ω
Total gate charge	Qg *	-	8.4	11.8	nC	V _{DD} ≒15V
Gate-source charge	Q _{gs} *	_	1.9	_	nC	V _{GS} =5V
Gate-drain charge	Q _{gd} *	-	3.3	_	nC	I _D =7.0A

^{*}Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C) < It is the same characteristics for the Tr1 and Tr2.>

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	V _{SD} *	_	_	1.2	V	I _S =6.4A, V _{GS} =0V

^{*}Pulsed



Electrical characteristic curves

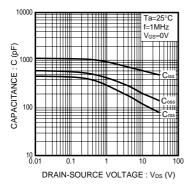


Fig.1 Typical Capacitance vs. Drain-Source Voltage

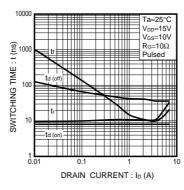


Fig.2 Switching Characteristics

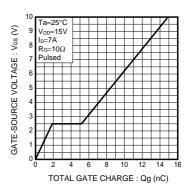


Fig.3 Dynamic Input Characteristics

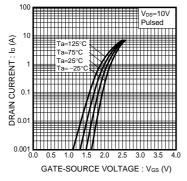


Fig.4 Typical Transfer Characteristics

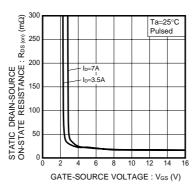


Fig.5 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

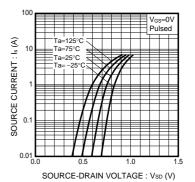


Fig.6 Source Current vs. Source-Drain Voltage

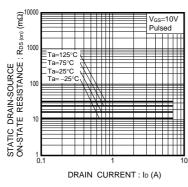


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current (I)

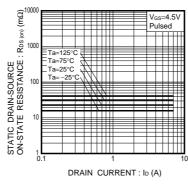


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current (II)

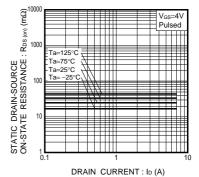


Fig.9 Static Drain-Source On-State Resistance vs. Drain Current (III)

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